



SW Test Workshop
Semiconductor Wafer Test Workshop

TPEG™ Mantis: a new solution for multiple advanced applications



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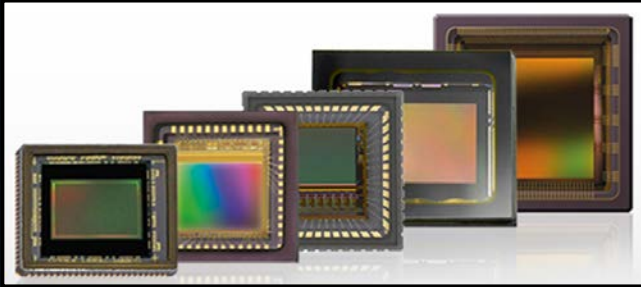
June 3-6, 2018

Overview

- Applications requirements
- TPEG™ Mantis concept
- TPEG™ Mantis general characteristics
- STM experience on field
- Summary

Applications Requirements

- Customer device applications for TPEG™ MEMS MANTIS



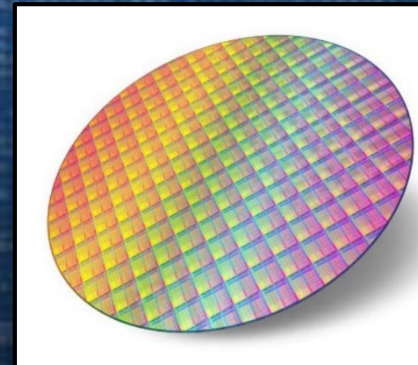
CMOS Image **Sensors**



NOR and NAND **Memories**



Consumer, Industrial and Auto
μControllers & LCD Drivers



Parametric Test (WAT, eTest, T84, ...)

Applications Requirements

- **General characteristics requested for CIS and Parametric Tests**
 - Mechanical solution that allows the passage of light through the probe card for the Imaging Sensor stimulation
 - Possibility to mount lens or diffusers in the Probe Card
 - Small scrub marks and low PAD damage
 - Controlled production of debris
 - Direct Attach solutions to minimize Probe Card cost
 - Low Signal attenuation up to 1.2 GHz
 - Good probe to probe insulation

TPEG Mantis Concept

- **Mantis probe concept**

- Mantis is a μ Cantilever needle using Technoprobe TPEG™ MEMS Technology. It merges the benefits of both technologies: Vertical and Cantilever.
- The inspiration came from...

...Nature

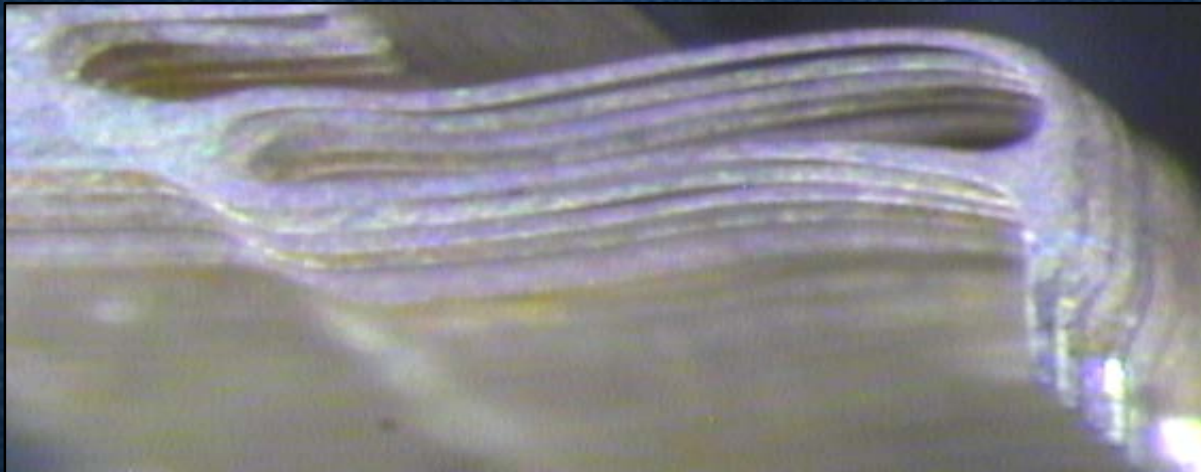


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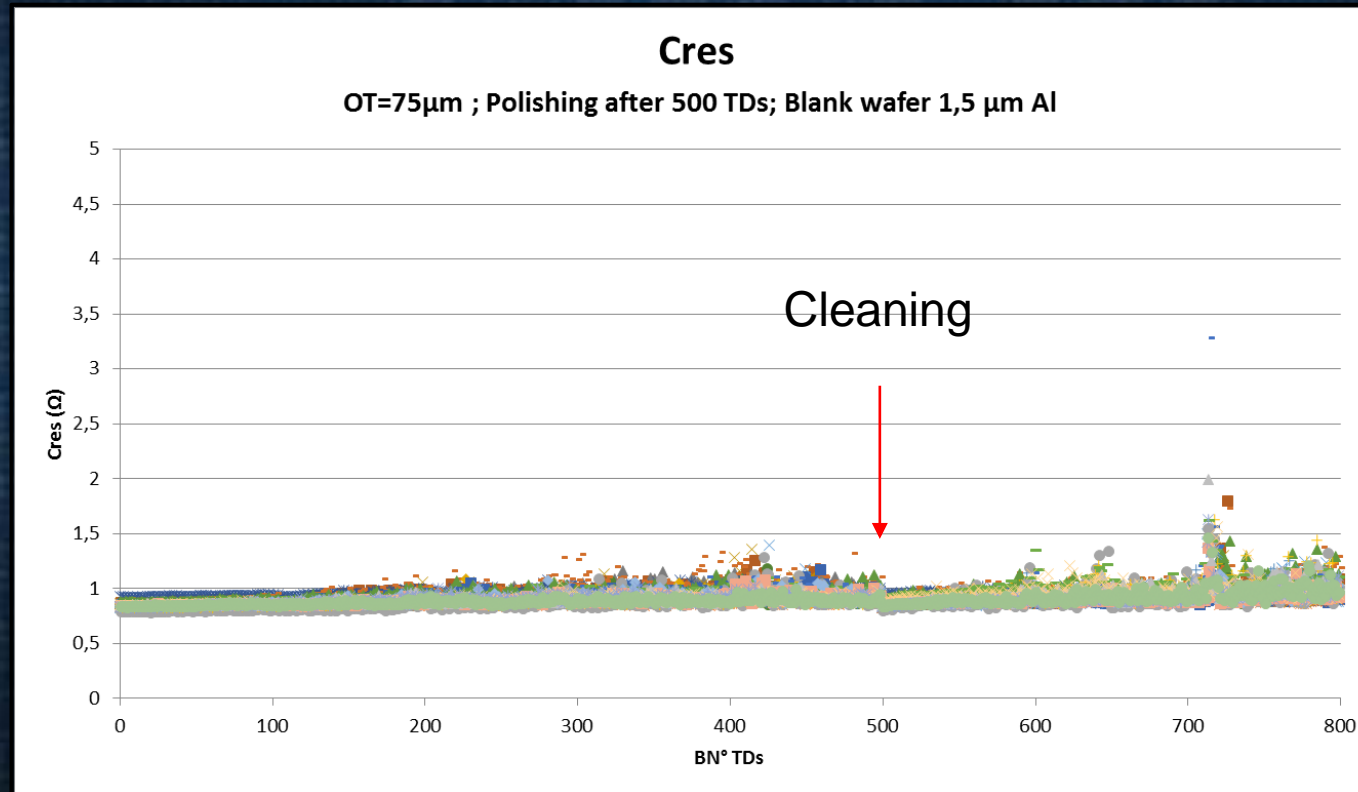
TPEG™ Mantis Internal qualification

- **Tests performed for the internal qualification**

- Mechanical Test:
 - Resistance to fatigue with 1M TDs at 120 μm Overdrive and 100K TDs on wafer edge
- Cres Test on Blank wafer.
- Scrub Analysis
- Probe Current Capability
- RF Simulation
- Test on Customer Field:
 - Pad damage analyses, Testing Yield evaluation, Life on field evaluation, etc...

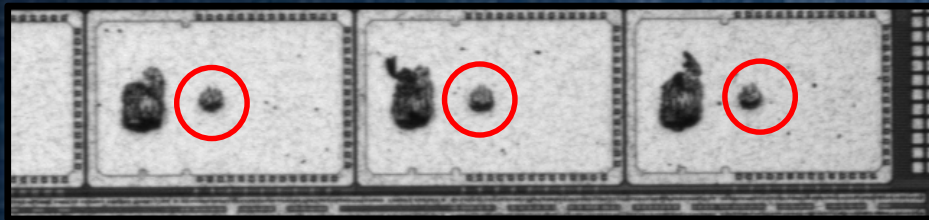
Cres Test

- Cres Test performed at OT=75 μm on Al Blank wafer (Al thickness 1,5 μm)
- Cleaning done after 500 TDs

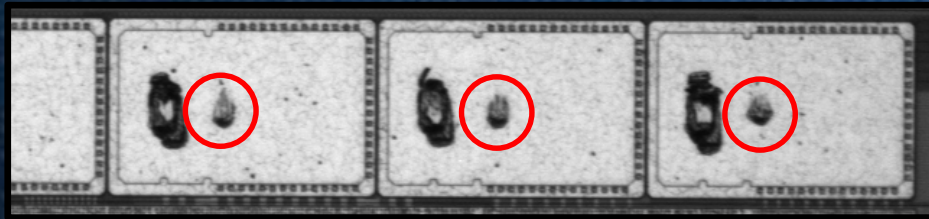


Scrub analyses Vs. Temperature

- **TPEG™ Mantis scrub marks on Al Pad at different temperatures**
 - TPEG™ Mantis scrub mark highlighted with the red circle.



OT=75 μm T= -40°C



OT=75 μm T= 60°C



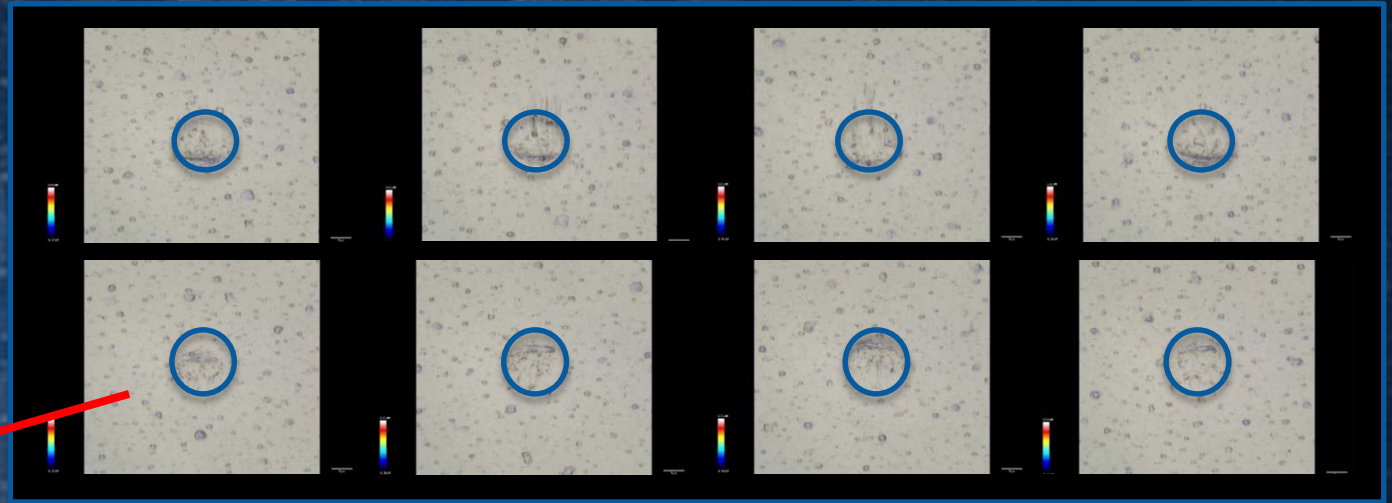
OT=75 μm T= 105°C

Scrub analyses

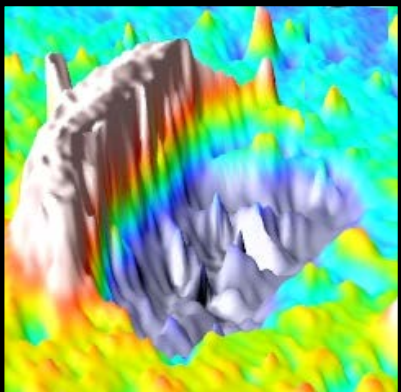
- Statistical scrub marks collected on Al blank wafer with thickness of $1.5\mu\text{m}$ at 50 and $100\mu\text{m}$ OD

OT= $50\mu\text{m}$

OT= $100\mu\text{m}$



- **Results:**

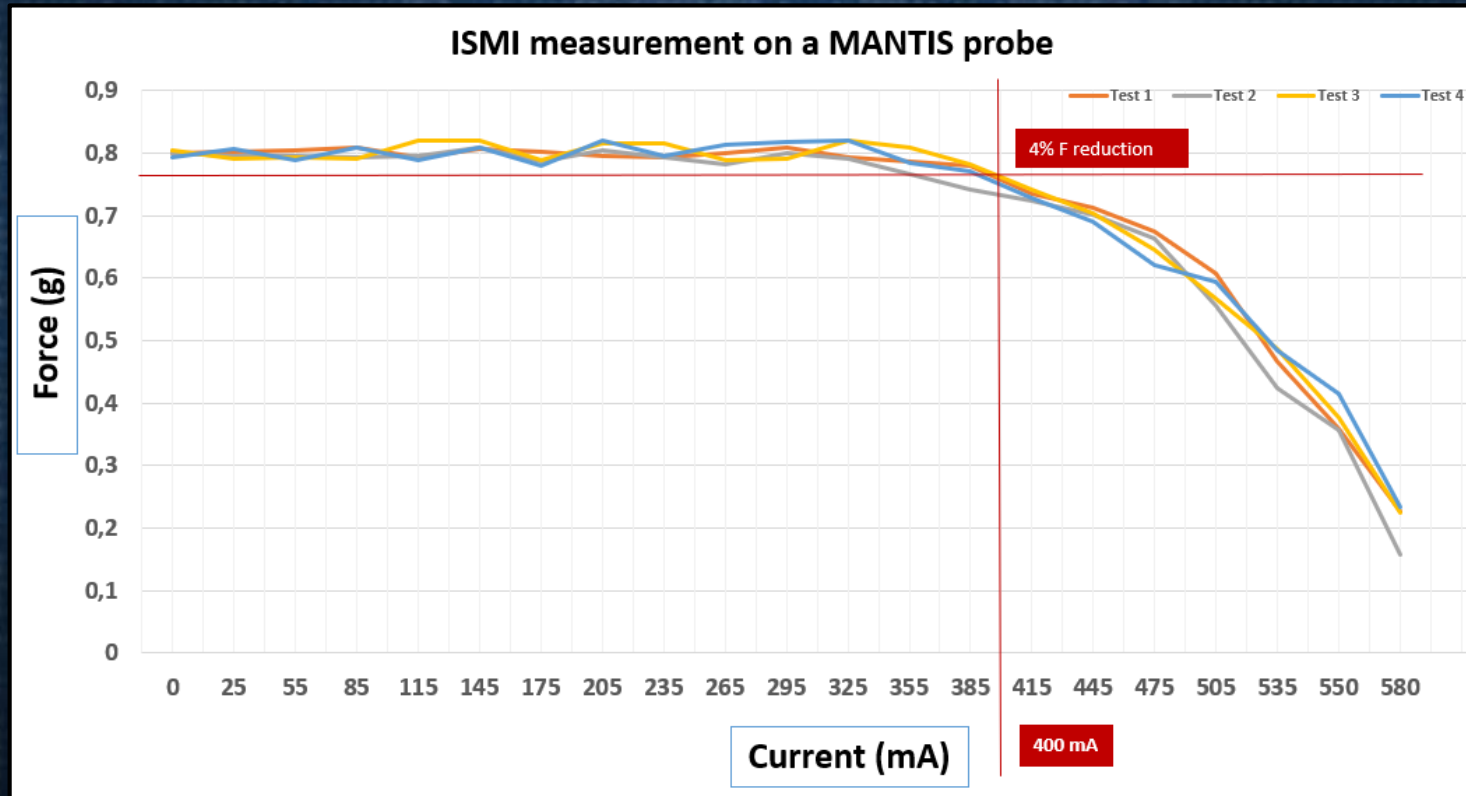


- At OT = $50\mu\text{m}$: Scrub length max = $16\mu\text{m}$, Scrub depth max = 290nm
- At OT = $100\mu\text{m}$: Scrub length max = $22\mu\text{m}$, Scrub depth max = 390nm

CCC analyses

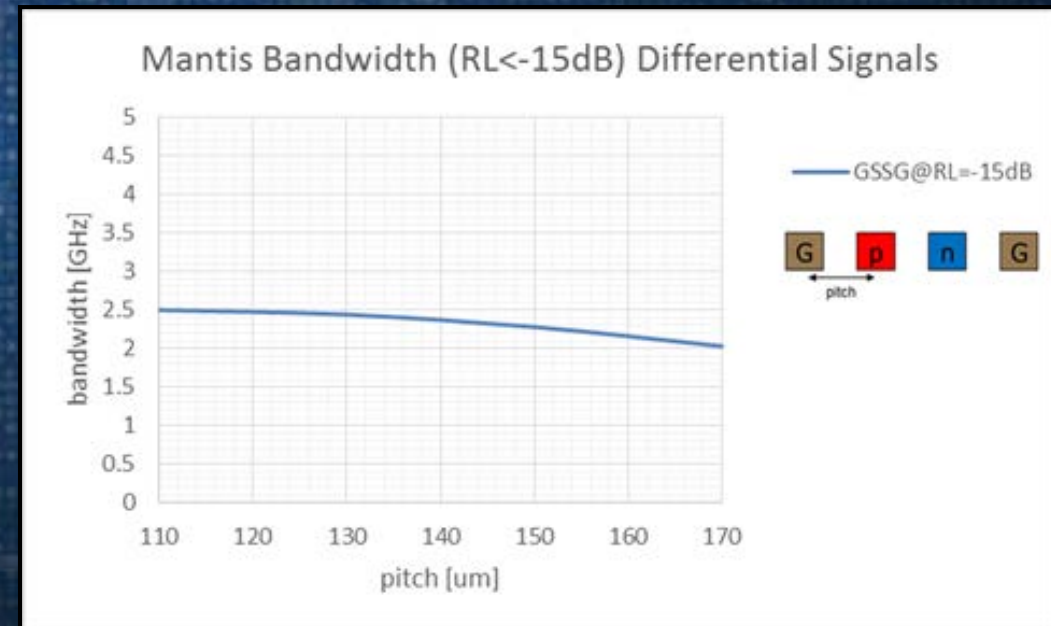
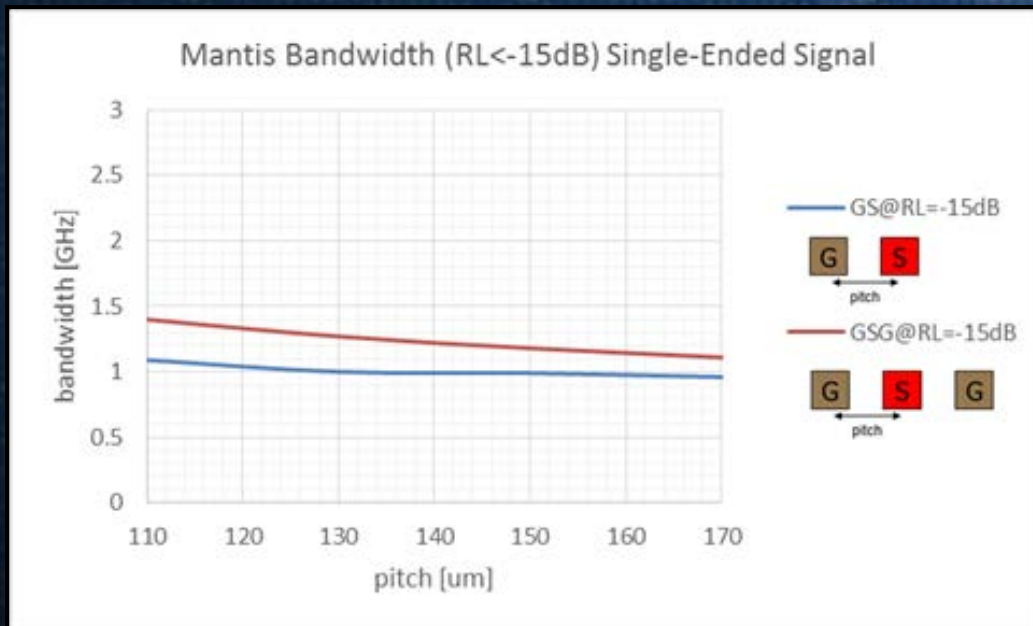
- **CCC performed with the ISMI 09 method**

- The current TPEG™ Mantis probe, has a 20% force reduction at 500 mA
- Max CCC limit at 4% of force reduction is 400 mA. This is the limit for TPEG™ Mantis probe
- The CCC can be increased customizing the probe.



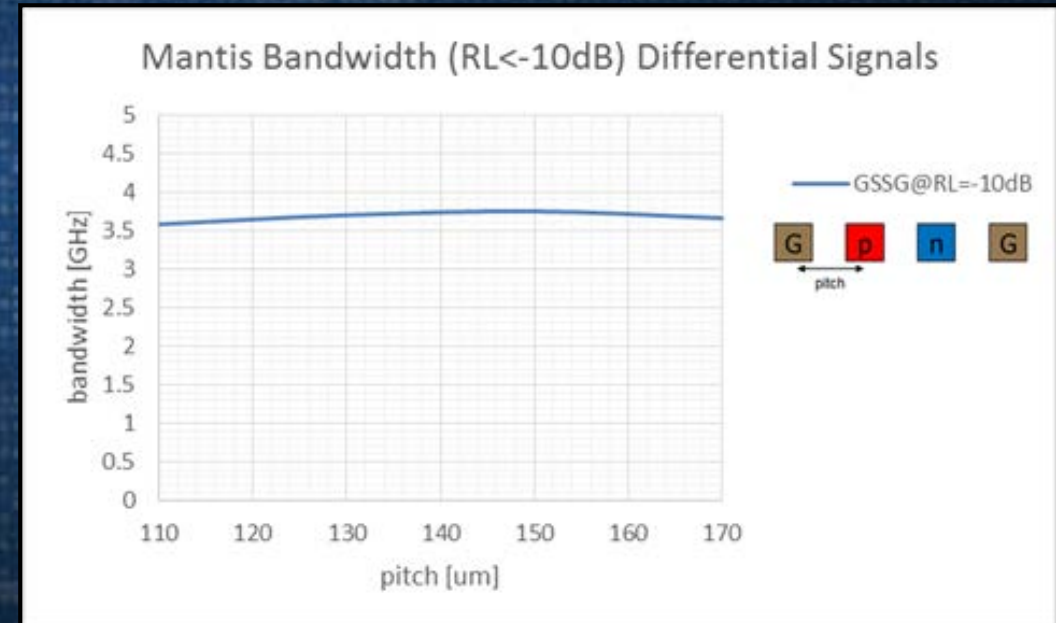
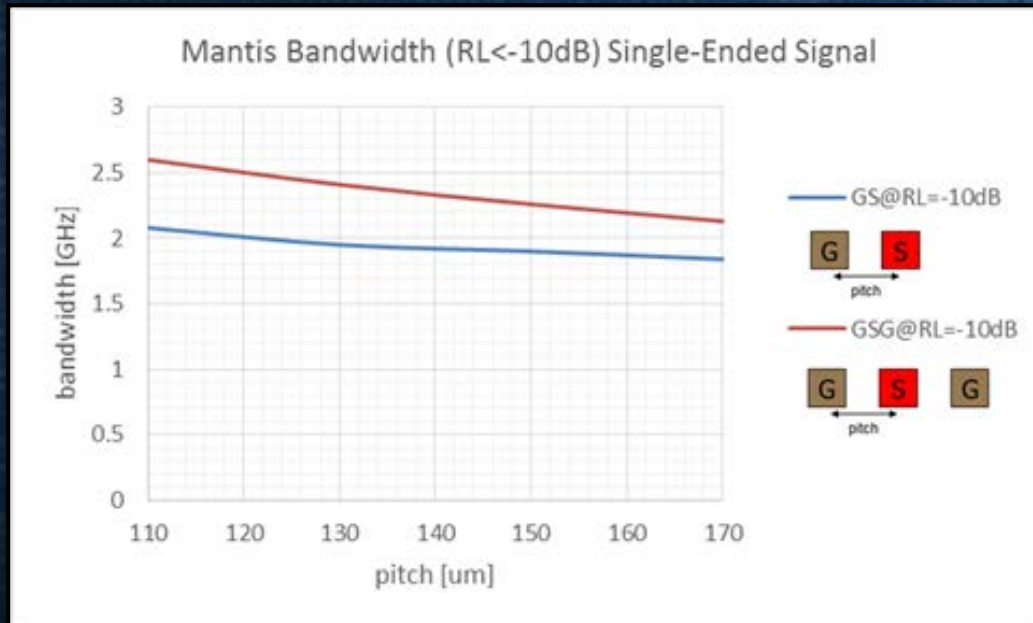
RF Simulations (Return Loss ≤ 15 dB)

- **Technoprobe performed RF simulations with different kind pitches and Signal modes.**
 - TPEG Mantis bandwidth has been simulated with different configurations.
 - The RL is maintained under 15 dB at 1 GHz for a large pitch window with Single Ended Signals and 2 GHz with Differential Signals.



RF Simulations (Return Loss $\leq 15\text{dB}$)

- **Technoprobe performed RF simulations with different kind pitches and Signal modes.**
 - TPEG Mantis bandwidth has been simulated with different configurations.
 - The RL is maintained under 10 dB at 1,8 GHz for a large pitch window with Single Ended Signals and 3.5 GHz with Differenzial Signals.



TPEG Mantis Description

- **Target Key Values**

- Low Force
- Low Pad Damage with controlled and limited scrub mark in all the OD range
- X and Y alignment comparable to Vertical MEMS Needle
- Good Z planarity comparable to high end Vertical MEMS Needle
- Possible to use Direct Attach PCB or Interposer (no need of complex and high costs MLOs or MLCs)
- Low constraints in layout capability
- Same tip size during entire lifetime
- Good Current Carrying Capability that can be customized.
- High parallelism

TPEG Mantis Specs

PARAMETER	TPEG™ MEMS MANTIS
Contact Diameter	16±4 µm
Usable Tip Length	> 200µm
Max pin count	> 20.000 pins
X, Y alignment accuracy and Z planarity	X,Y ± 10 µm; Z electrical plan Δ 20 µm
Min pitch and configuration	50µm linear configuration ^(Probes from 2 directions)
Pin Current (CCC ISMI 2009)	400 mA
Force (at 75µm OD)	3.0 g
Working OD / Max OD	75µm / 100 µm

STMicroelectronics Experience



STM Microelectronics qualification criteria

- **STM used a High Volume product for qualification and benchmark of Mantis technology vs. STM standard one. ST qualification conditions:**
 - No PAD damaged at maximum OT and maximum number of passes
 - No crack under PAD at maximum OT and maximum number of passes
 - Scrub marks size and position within spec
 - Yield aligned (or better) to standard production card
 - No “special requirement” for cleaning
 - The above conditions to be verified at 0-time and after production (150kTDs)

STM evaluation plan

MANTIS

Phase 0

Phase 1

HVM

T0 – Incoming:

- Probe card information summary and qualification data
- Electrical and mechanical analysis and qualification
- Probing DOE results
- Conclusion

T1 - 150kTDs:

- Probe card information summary and qualification data
- Electrical and mechanical analysis and qualification
- Probing DOE results
- Conclusion

TF – 1M TD:

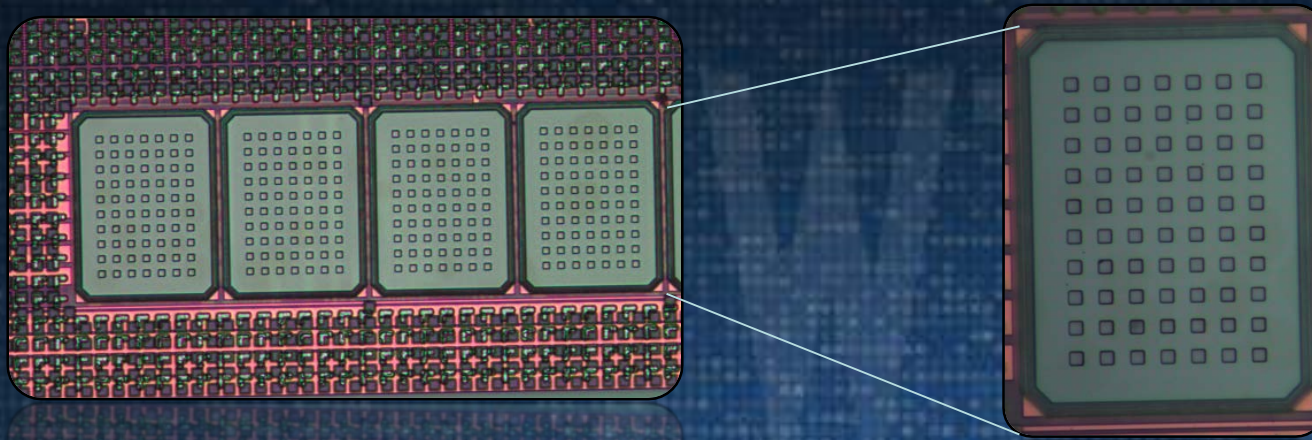
- Lifetime Evaluation
- Uptime Evaluation
- Conclusion

Before starting

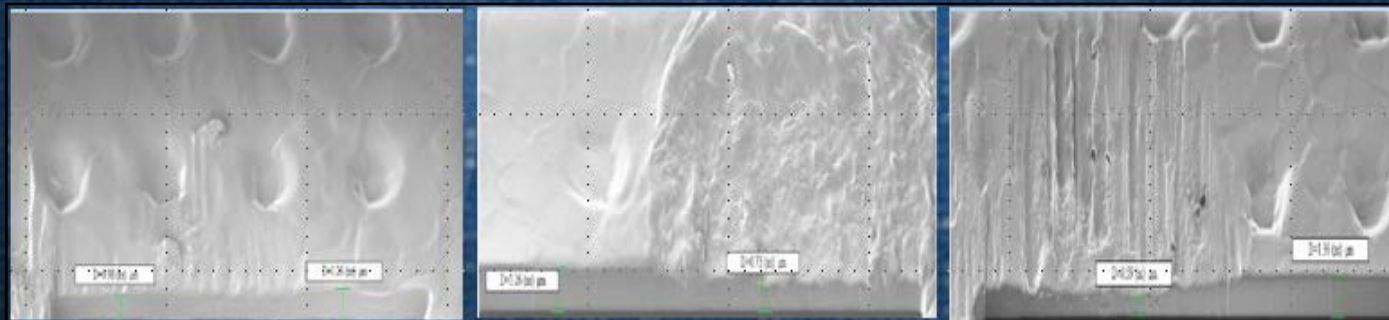
- **Probecard design**
 - X16 DUTs
 - 320 springs
- **Working overdrive**
 - 80 μ m
- **T0 and T1 probing DOE conditions**
 - Number of passes: 12
 - Overdrive from 60 μ m to 120 μ m
- **Cleaning material**
 - ITS PP150



PAD damage evaluation at T0



No crack under
passivation under
worst conditions
OD=120 μ m (with
12passes)



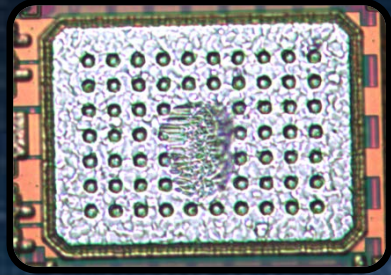
OD=80 μ m/12passes
Scrub depth 280nm

OD=100 μ m/12passes
Scrub depth 530nm

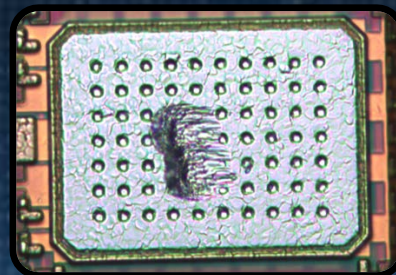
OD=120 μ m/12passes
Scrub depth 770nm

No crack under
passivation under
worst conditions

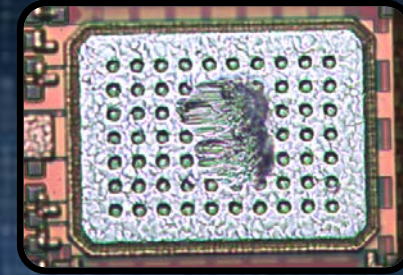
Scrub mark evaluation at T0



OD=80µm
12 passes



OD=100µm
12 passes

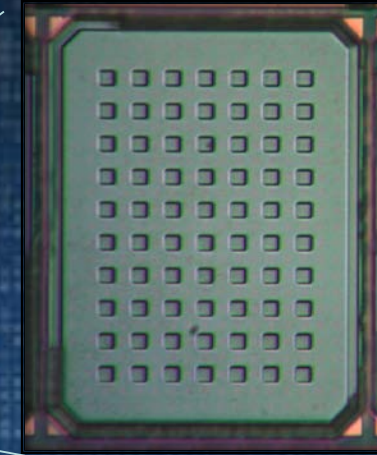
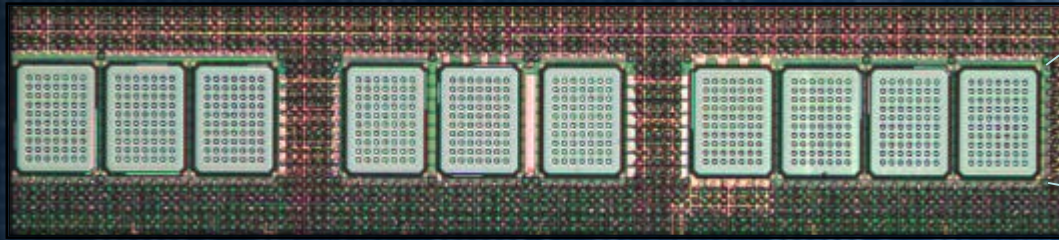


OD=120µm
12 passes

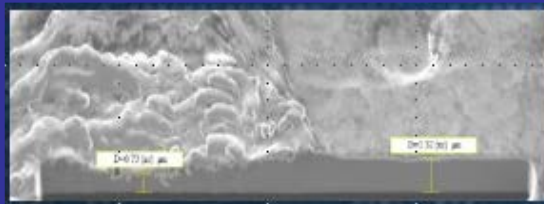
OD	PAD edge Y-margin Cpk	PAD edge X-margin Cpk	Scrub Length Cp	Scrub Width Cp
60µm	6.80	5.00	2.68	3.03
80µm	7.28	3.25	3.46	3.01
100µm	9.06	3.01	3.45	4.03
120µm	3.31	3.03	4.82	2.69

**Scrub marks area under worst conditions within spec
(<400µm² vs. 3400µm² Square Bonding PAD size)**

PAD damage evaluation at T1=150kTDs



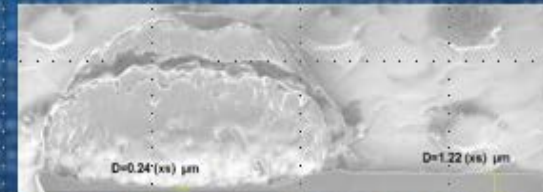
No damage under metal layer with the worst conditions OD=120 μ m (with 12passes)



OD=80 μ m/12passes
Scrub depth 580nm



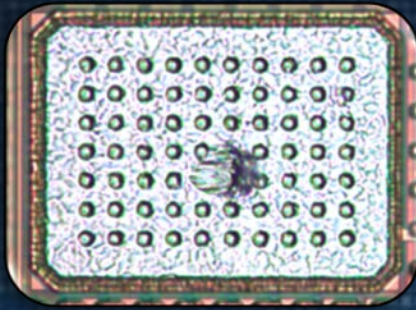
OD=100 μ m/12passes
Scrub depth 890nm



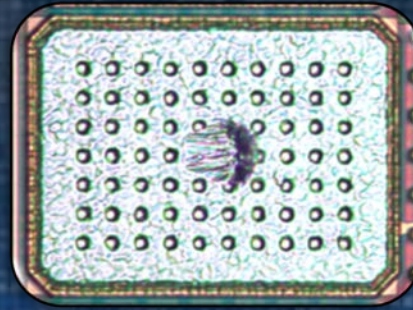
OD=120 μ m/12passes
Scrub depth 970nm

No damage under metal layer under worst conditions

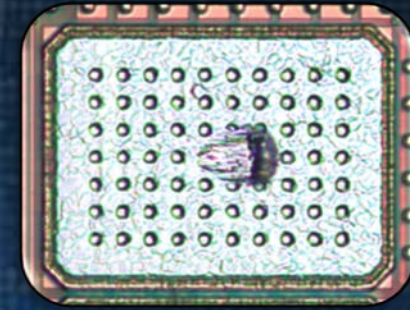
Scrub mark evaluation at T1=150kTDs



OD=80μm
12 passes



OD=100μm
12 passes



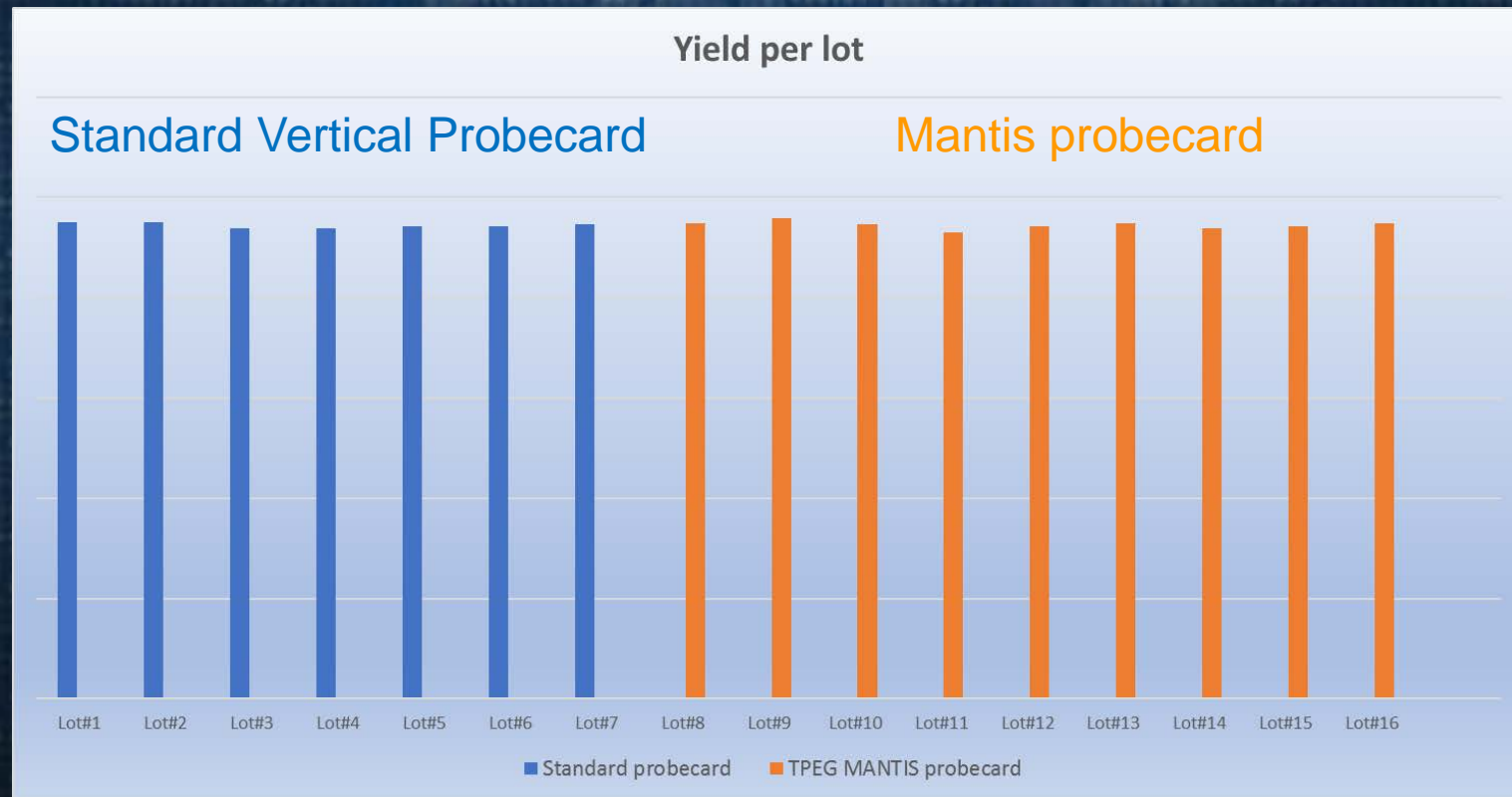
OD=120μm
12 passes

OD	PAD edge Y- margin Cpk	PAD edge X-margin Cpk	Scrub Length Cp	Scrub Width Cp
80μm	5.04	4.28	4.02	3.01
100μm	8.77	6.75	2.43	3.43
120μm	9.45	5.06	4.8	4.02

**Scrub marks area under worst conditions within spec
(<400μm² vs. 3400μm² Square Bonding PAD size)**

Yield benchmark from T0 to T1 to today

- The probecard is in production since end of 2017 with the same cleaning material as the reference probecard



Yield aligned to
standard
production solution

STM Conclusion

- **Qualification**

- TPEG MEMS Mantis probecard passed all the qualification criteria

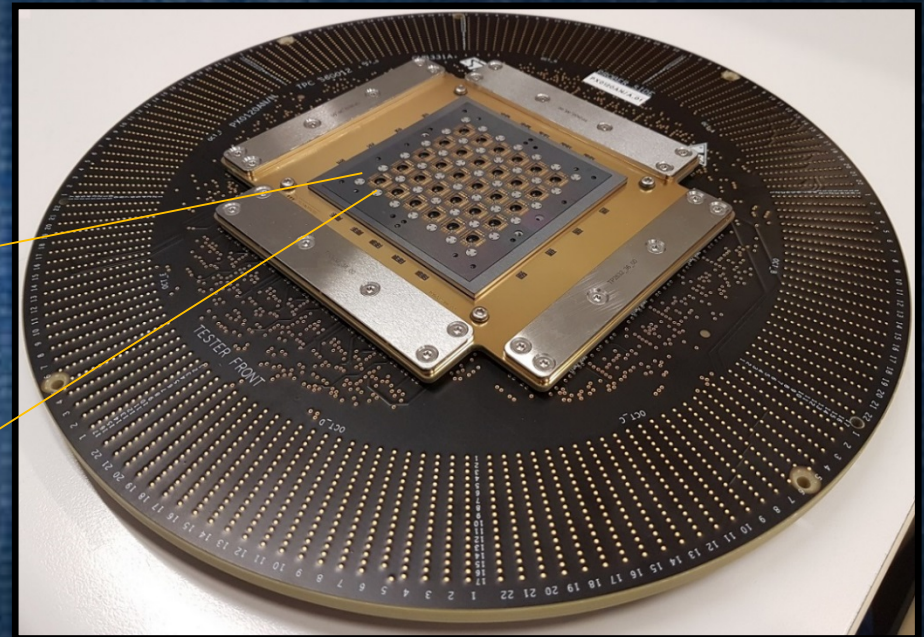
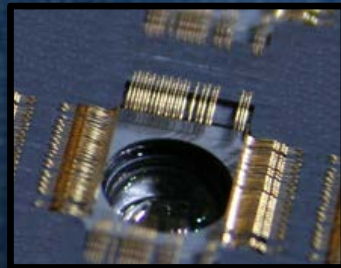
- **High Volume production**

- TPEG MEMS Mantis probecard is in production since end of 2017
- It reached 1.2MTDs without any issue so far
- Uptime 99%
- Tip consumption 30 μ m (on total 220 μ m usable tip)
- We will keep monitoring it...

Next

- **CMOS Image Sensor probecard**

- 3600 probes
- x30
- Status: in qualification



Thanks for your Support !

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